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# Pin Configuration

### Figure 1. 28-pin DIP / SOJ pinout (Top View)

DIP/SOJ Top View					
NC 44 A5 A6 A7 A9 H10 A11 I/O1 I/O1 I/O1 I/O2 GND	1 2 3 4 5 6 6 7 8 9 10 11 11 2 13 14	28 Vcc 27 WE 26 CE <sub>2</sub> 25 A <sub>3</sub> 24 A <sub>2</sub> 23 A <sub>1</sub> 22 DE 21 OE 21 OE 21 OE 21 VO 6 19 VO 19 VO 10 19 VO 10 10 10 10 10 10 10 10 10 10 10 10 10			

# **Selection Guide**

Description	-15	-20	-35
Maximum Access Time (ns)	15	20	35
Maximum Operating Current (mA)	130	110	100
Maximum CMOS Standby Current (mA)	15	15	15



### **Maximum Ratings**

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature65 °C to +150 °C
Ambient temperature with power applied–55 °C to +125 °C
Supply voltage to ground potential–0.5 V to +7.0 V
DC voltage applied to outputs in High Z State $^{\left[2\right]}$ 0.5 V to +7.0 V
DC input voltage <sup>[2]</sup> 0.5 V to +7.0 V

Output current into outputs (LOW)	nΑ
Static discharge voltage	
(per MIL-STD-883, Method 3015) >2001	V
Latch-up current	nΑ

### **Operating Range**

Range	Ambient Temperature	V <sub>cc</sub>
Commercial	0 °C to +70 °C	$5~V\pm10\%$
Industrial	–40 °C to +85 °C	$5 \text{ V} \pm 10\%$

### **Electrical Characteristics**

Over the Operating Range

Parameter Description		Description Test Conditions		-15	-20		-35		Unit
Parameter	Description	Test Conditions	Min	Max	Min	Max	Min	Max	Unit
V <sub>OH</sub>	Output HIGH Voltage	$V_{CC}$ = Min., $I_{OH}$ = -4.0 mA	2.4	-	2.4	-	2.4	-	V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA	_	0.4	_	0.4	_	0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub> + 0.3	2.2	V <sub>CC</sub> + 0.3	2.2	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW Voltage [2]		-0.5	0.8	-0.5	0.8	-0.5	0.8	V
I <sub>IX</sub>	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-5	+5	-5	+5	-5	+5	μA
I <sub>OZ</sub>	Output Leakage Current	$\begin{array}{l} GND \leq V_I \leq V_{CC}, \\ Output \ Disabled \end{array}$	-5	+5	-5	+5	-5	+5	μΑ
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max., I <sub>OUT</sub> = 0 mA	_	130	-	110	_	100	mA
I <sub>SB1</sub>	Automatic Power-down Current	$\label{eq:max_CC} \begin{array}{l} \mbox{Max. V}_{CC}, \\ \hline \hline \hline CE_1 \geq V_{IH} \mbox{ or } CE_2 \leq V_{IL}, \\ \mbox{Min. Duty Cycle = 100\%} \end{array}$	_	40	_	20	_	20	mA
I <sub>SB2</sub>	Automatic Power-down Current	$\label{eq:max_constraint} \begin{array}{l} \mbox{Max. V}_{CC}, \\ \hline \overline{CE}_1 \geq V_{CC} - 0.3 \ \mbox{V or} \\ CE_2 \leq 0.3 \ \mbox{V}, \\ \hline V_{IN} \geq V_{CC} - 0.3 \ \mbox{V or} \\ \hline V_{IN} \leq 0.3 \ \mbox{V} \end{array}$	-	15	_	15	_	15	mA

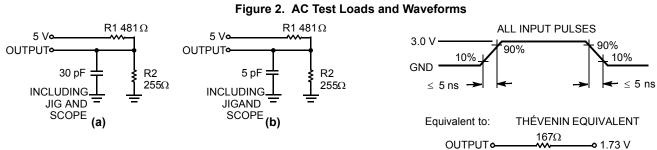
Note 2. Minimum voltage is equal to -3.0 V for pulse durations less than 30 ns.



### Capacitance

Parameter <sup>[3]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = 5.0 V	7	pF
C <sub>OUT</sub>	Output capacitance		7	pF

## AC Test Loads and Waveforms





### **Switching Characteristics**

Over the Operating Range

<b>D</b> [4]		-	15	-:	20	-3	85	
Parameter <sup>[4]</sup> Description		Min	Max	Min	Max	Min	Max	Unit
Read Cycle								
t <sub>RC</sub>	Read Cycle Time	15	-	20	-	35	-	ns
t <sub>AA</sub>	Address to Data Valid	_	15	-	20	_	35	ns
t <sub>OHA</sub>	Data Hold from Address Change	3	_	5	_	5	_	ns
t <sub>ACE1</sub>	CE <sub>1</sub> LOW to Data Valid	_	15	-	20	_	35	ns
t <sub>ACE2</sub>	CE <sub>2</sub> HIGH to Data Valid	_	15	-	20	_	35	ns
t <sub>DOE</sub>	OE LOW to Data Valid	_	8	-	9	_	15	ns
t <sub>LZOE</sub>	OE LOW to Low Z	3	_	3	_	3	_	ns
t <sub>HZOE</sub>	OE HIGH to High Z <sup>[5]</sup>	_	7	-	8	_	10	ns
t <sub>LZCE1</sub>	CE <sub>1</sub> LOW to Low Z <sup>[6]</sup>	3	-	5	-	5	-	ns
t <sub>LZCE2</sub>	CE <sub>2</sub> HIGH to Low Z	3	-	3	-	3	-	ns
t <sub>HZCE</sub>	$\overline{CE}_1$ HIGH to High Z <sup>[5, 6]</sup> CE <sub>2</sub> LOW to High Z	-	7	-	8	-	10	ns
t <sub>PU</sub>	CE <sub>1</sub> LOW to Power-up CE <sub>2</sub> to HIGH to Power-up	0	_	0	-	0	_	ns
t <sub>PD</sub>	CE <sub>1</sub> HIGH to Power-down CE <sub>2</sub> LOW to Power-down	_	15	-	20	-	20	ns
Write Cycle [7	7, 8]					1		
t <sub>WC</sub>	Write Cycle Time	15	-	20	-	35	-	ns
t <sub>SCE1</sub>	CE <sub>1</sub> LOW to Write End	12	-	15	-	20	-	ns
t <sub>SCE2</sub>	CE <sub>2</sub> HIGH to Write End	12	_	15	_	20	_	ns
t <sub>AW</sub>	Address Setup to Write End	12	_	15	_	25	_	ns
t <sub>HA</sub>	Address Hold from Write End	0	-	0	-	0	-	ns
t <sub>SA</sub>	Address Setup to Write Start	0	-	0	-	0	-	ns
t <sub>PWE</sub>	WE Pulse Width	12	-	15	_	20	-	ns
t <sub>SD</sub>	Data Setup to Write End	8	-	10	_	12	-	ns
t <sub>HD</sub>	Data Hold from Write End	0	-	0	_	0	-	ns
t <sub>HZWE</sub>	WE LOW to High Z <sup>[5]</sup>	_	7	_	7	-	8	ns
t <sub>LZWE</sub>	WE HIGH to Low Z	3	_	5	_	5	_	ns

### Notes

Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and 30-pF load capacitance.

5.  $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with  $C_L$  = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage.

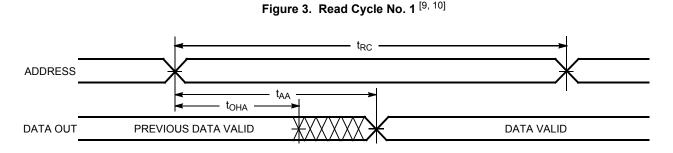
6. At any temperature and voltage condition,  $t_{\text{HZCE}}$  is less than  $t_{\text{LZCE1}}$  and  $t_{\text{LZCE2}}$  for any given device.

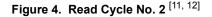
7. The internal write time of the memory is defined by the overlap of CE<sub>1</sub> LOW, CE<sub>2</sub> HIGH, and WE LOW. All 3 signals must be active to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing must be referenced to the rising edge of the signal that terminates the write.

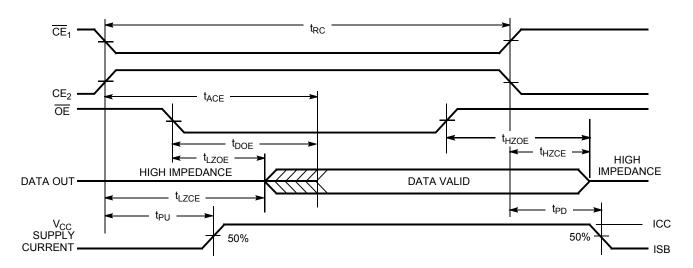
8. The minimum write cycle pulse width of Write cycle No. 3 (WE Controlled, OE LOW) should be equal to sum t<sub>HZWE</sub> and t<sub>SD</sub>.



**Switching Waveforms** 





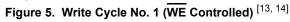


#### Notes

- 9. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}_1 = V_{IL}$ .  $CE_2 = V_{IH}$ .
- 10.  $\overline{\text{WE}}$  is HIGH for read cycle.
- 11. Data I/O is High Z if  $\overline{OE} = V_{IH}$ ,  $\overline{CE}_1 = V_{IH}$ ,  $\overline{WE} = V_{IL}$ , or  $CE_2 = V_{IL}$ .
- 12. The internal write time of the memory is defined by the overlap of CE<sub>1</sub> LOW, CE<sub>2</sub> HIGH and WE LOW. CE<sub>1</sub> and WE must be LOW and CE<sub>2</sub> must be HIGH to initiate write. A write can be terminated by CE<sub>1</sub> or WE going HIGH or CE<sub>2</sub> going LOW. The data input setup and hold timing must be referenced to the rising edge of the signal that terminates the write.



### Switching Waveforms (continued)



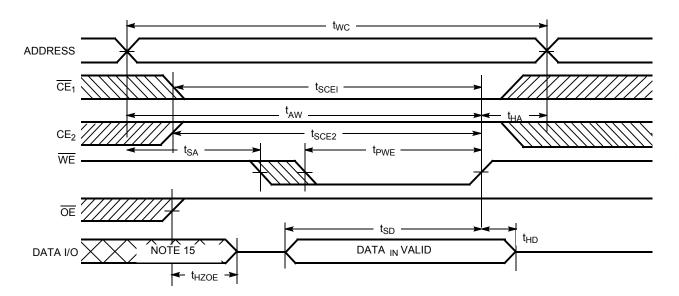
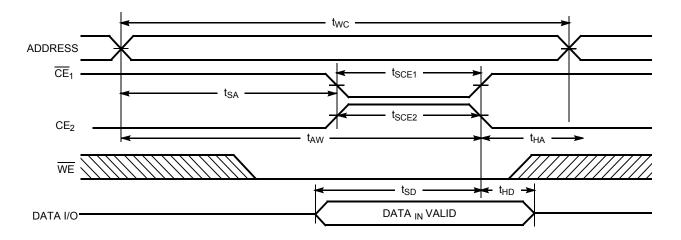


Figure 6. Write Cycle No. 2 (CE Controlled) <sup>[14, 15, 16]</sup>



Notes 13. WE is HIGH for read cycle.

14. The internal write time of the memory is defined by the overlap of  $\overline{CE}_1$  LOW,  $CE_2$  HIGH and  $\overline{WE}$  LOW.  $\overline{CE}_1$  and  $\overline{WE}$  must be LOW and  $CE_2$  must be HIGH to initiate write. A write can be terminated by  $\overline{CE}_1$  or WE going HIGH or  $CE_2$  going LOW. The data input setup and hold timing must be referenced to the rising edge of the signal that terminates the write.

15. During this period, the I/Os are in the output state and input signals must not be applied.

16. The minimum write cycle time for Write Cycle #3 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW) is the sum of t<sub>HZWE</sub> and t<sub>SD</sub>.



### Switching Waveforms (continued)

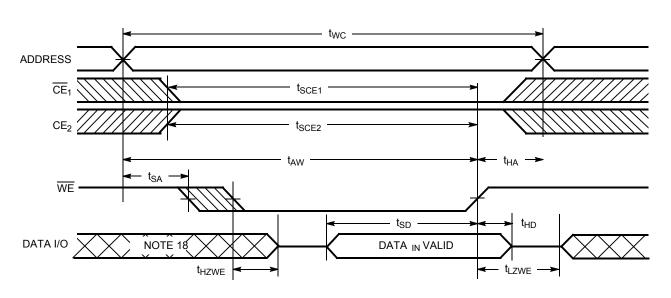


Figure 7. Write Cycle No. 3 (WE Controlled,  $\overline{\text{OE}}$  LOW) [17, 19, 20]

#### Notes

17. The internal write time of the memory is defined by the overlap of CE<sub>1</sub> LOW, CE<sub>2</sub> HIGH and WE LOW. CE<sub>1</sub> and WE must be LOW and CE<sub>2</sub> must be HIGH to initiate write. A write can be terminated by CE<sub>1</sub> or WE going HIGH or CE<sub>2</sub> going LOW. The data input setup and hold timing must be referenced to the rising edge of the signal that terminates the write.

20. If  $\overline{\text{CE}}_1$  goes HIGH or  $\text{CE}_2$  goes LOW simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in a high-impedance state.

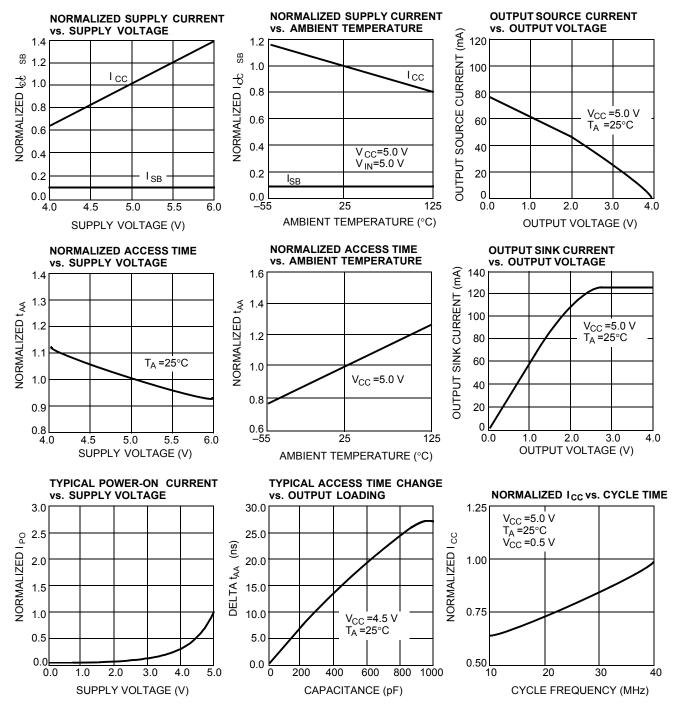
<sup>18.</sup> During this period, the I/Os are in the output state and input signals must not be applied.

<sup>19.</sup> The minimum write cycle time for Write Cycle #3 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW) is the sum of t<sub>HZWE</sub> and t<sub>SD</sub>.





### **Typical DC and AC Characteristics**







## Truth Table

CE <sub>1</sub>	$CE_2$	WE	OE	Input/Output	Mode
н	Х	Х	Х	High Z	Deselect/ Power-down
X	L	Х	Х	High Z	Deselect/ Power-down
L	Н	Н	L	Data Out	Read
L	Н	L	Х	Data In	Write
L	Н	Н	Н	High Z	Deselect

# Address Designators

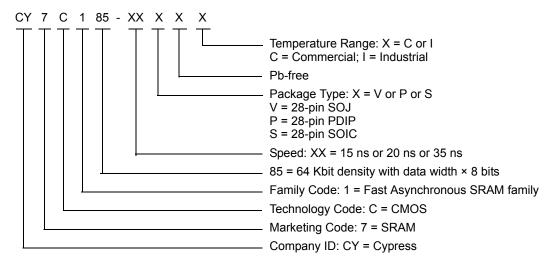
Address Name	Address Function	Pin Number
A4	X3	2
A5	X4	3
A6	X5	4
A7	X6	5
A8	X7	6
A9	Y1	7
A10	Y4	8
A11	Y3	9
A12	Y0	10
A0	Y2	21
A1	X0	23
A2	X1	24
A3	X2	25



### **Ordering Information**

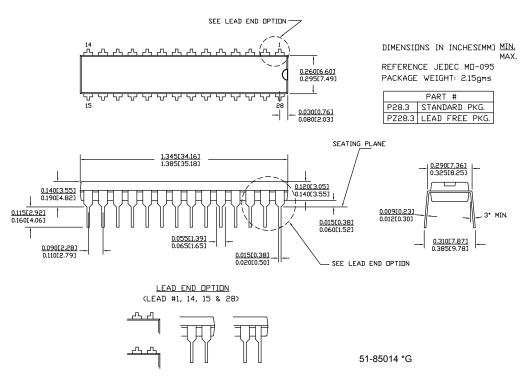
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C185-15VI	51-85031	28-pin SOJ	Industrial
20	CY7C185-20PXC	51-85014	28-pin PDIP (Pb-free)	Commercial

### **Ordering Code Definitions**





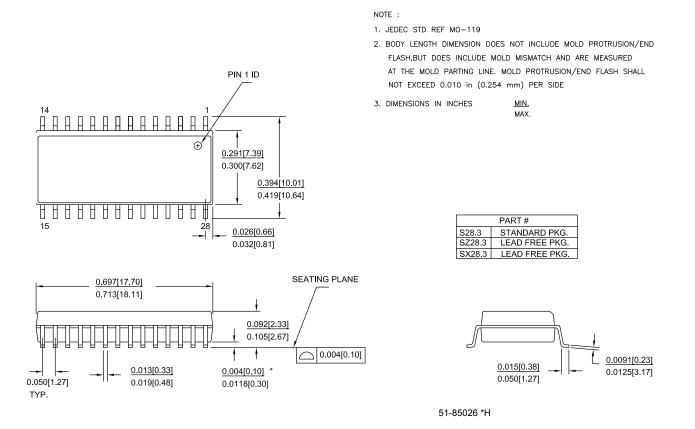
### Package Diagrams





### Package Diagrams (continued)

### Figure 9. 28-pin SOIC (0.713 × 0.300 × 0.0932 Inches) Package Outline, 51-85026



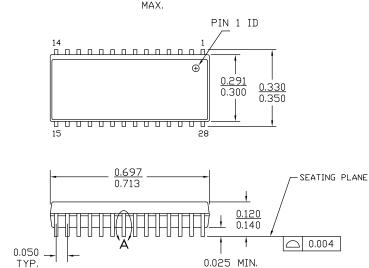


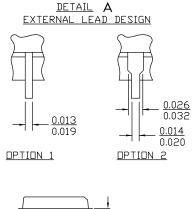
### Package Diagrams (continued)

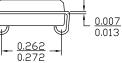


NDTE :

- 1. JEDEC STD REF MO088
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
- MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE 3. DIMENSIONS IN INCHES MIN. MAX.







51-85031 \*E



### Acronyms

Acronym	Description		
CE	Chip Enable		
CMOS	Complementary Metal Oxide Semiconductor		
I/O Input/Output			
OE	Output Enable		
SRAM	Static Random Access Memory		
SOJ	Small Outline J-Lead		
TSOP	Thin Small Outline Package		
VFBGA	Very Fine-Pitch Ball Grid Array		
WE	Write Enable		

### **Document Conventions**

### **Units of Measure**

Symbol	Unit of Measure	
°C	degree Celsius	
MHz	megahertz	
μA	microampere	
mA	milliampere	
mV	millivolt	
mW	milliwatt	
ns	nanosecond	
pF	picofarad	
V	volt	
W	watt	





# **Document History Page**

Document Title: CY7C185, 64-Kbit (8 K × 8) Static RAM Document Number: 38-05043					
Revision	ECN	Submission Date	Orig. of Change	Description of Change	
**	107145	09/10/01	SZV	Change from Spec number: 38-00037 to 38-05043	
*A	116470	09/16/02	CEA	Add applications foot note to data sheet	
*В	486744	See ECN	NXR	Changed Low standby power from 220 mW to 85 mW Changed the description of $I_{ X}$ from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed $I_{OS}$ parameter from DC Electrical Characteristics table Updated the Ordering Information table	
*C	2263686	See ECN	VKN / AESA	Removed 25 ns speed bin Updated the Ordering Information table as per the current product offerings	
*D	3105329	12/09/2010	AJU	Added Ordering Code Definitions. Updated Package Diagrams.	
*E	3235800	04/20/2011	PRAS	Updated package diagram spec 51-85026 to *F. Added Acronyms and Units of Measure. Template changes.	
*F	4383597	05/19/2014	VINI	Updated Switching Characteristics: Added Note 8 and referred the same note in "Write Cycle". Updated Package Diagrams: spec 51-85014 – Changed revision from *E to *G. spec 51-85026 – Changed revision from *F to *H. spec 51-85031 – Changed revision from *D to *E. Updated in new template. Completing Sunset Review.	
*G	4579569	11/26/2014	VINI	Added related documentation hyperlink in page 1. Removed the prune part number CY7C185-35SC in Ordering Information.	



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